

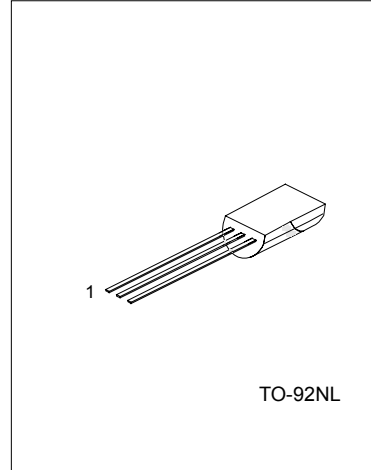
# UTC 2SA928A

# PNP EPITAXIAL SILICON TRANSISTOR

## AUDIO POWER AMPLIFIER

### FEATURES

- \*Collector Dissipation  $P_c=1$  W
- \*3 W Output Application
- \*Complement of 2SC2328A



1: EMITTER 2: COLLECTOR 3: BASE

### ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V <sub>CB0</sub>	-30	V
Collector-emitter voltage	V <sub>CEO</sub>	-30	V
Emitter-base voltage	V <sub>EB0</sub>	-5	V
Collector dissipation	P <sub>c</sub>	1	W
Collector current	I <sub>c</sub>	-2	A
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

### ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	BV <sub>CB0</sub>	I <sub>c</sub> =-100μA, I <sub>E</sub> =0	-30			V
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>c</sub> =-10mA, I <sub>B</sub> =0	-30			V
Emitter-base breakdown voltage	BV <sub>EB0</sub>	I <sub>E</sub> =-1mA, I <sub>c</sub> =0	-5			V
Collector cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> =-30V, I <sub>E</sub> =0			-100	nA
Emitter cut-off current	I <sub>EB0</sub>	V <sub>BE</sub> =-5V, I <sub>c</sub> =0			-100	nA
DC current gain(note)	h <sub>FE</sub>	V <sub>CE</sub> =-2V, I <sub>c</sub> =-500mA	100		320	
Base-emitter on voltage	V <sub>BE(on)</sub>	V <sub>CE</sub> =-2V, I <sub>c</sub> =-500mA			-1	V
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> =-1.5A, I <sub>B</sub> =-0.03A			-2	V
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10V, I <sub>E</sub> = 0, f=1MHz		48		pF
Current gain bandwidth product	f <sub>t</sub>	V <sub>CE</sub> =-2V, I <sub>c</sub> =-500mA		120		MHz

### CLASSIFICATION OF hFE

RANK	O	Y
RANGE	100-200	160-320

TYPICAL CHARACTERISTIC CURVES

